

In the Claims:

The claims are as follows:

1-8. (Canceled)

9. (Currently Amended) An electronic structure, comprising:

a substrate, wherein the substrate is selected from the group consisting of a ceramic chip carrier, an organic chip carrier, and a printed circuit board; and

a semiconductor device electrically coupled to the substrate, wherein the semiconductor device is divided into a plurality of segments, wherein at least one segment of the plurality of segments is not congruent with respect to a remaining segment of the plurality segments, and wherein the substrate comprises a coefficient of thermal expansion that is greater than a coefficient of thermal expansion of the semiconductor device.

10. (Original) The electronic structure of claim 9, wherein the length of each segment of the semiconductor device is greater than or equal to 5 millimeters.

11. (Original) The electronic structure of claim 9, wherein a first segment and a second segment of the plurality of segments are congruent with respect to each other.

12. (Canceled)

13. (Original) The electronic structure of claim 9, wherein the plurality of segments are square segments.

14-20. (Canceled)

21. (Previously presented) The electronic structure of claim 9, wherein the substrate is symmetrically coupled to each segment of the semiconductor device.

22. (Canceled)

23. (Previously presented) The electronic structure of claim 9, wherein the semiconductor device is a semiconductor chip.

24. (Canceled)

25. (Currently) A method for forming an electronic structure, comprising:

dividing a semiconductor device into a plurality of segments, and

electrically coupling a substrate to each segment of the plurality of segments of the semiconductor device, wherein the substrate is selected from the group consisting of a ceramic chip carrier, an organic chip carrier, and a printed circuit board, wherein at least one segment of the plurality of segments is not congruent with respect to a remaining segment of the plurality of segments, and wherein the substrate comprises a coefficient of thermal expansion that is greater

than a coefficient of thermal expansion of the semiconductor device.

26. (Previously presented) The method of claim 25, wherein each segment of the semiconductor device is symmetrically coupled to the substrate.

27. (Canceled)

28. (Previously presented) The method of claim 25, wherein a first segment and a second segment of the plurality of segments are congruent with respect to each other.

29. (Canceled)

30. (Previously presented) The method of claim 25, wherein the length of each segment of the semiconductor device is greater than or equal to 5 millimeters.

31. (Previously presented) The method of claim 25, wherein the plurality of segments are square segments.

32. (Previously presented) The method of claim 25, wherein the semiconductor device is a semiconductor chip.

33. (Canceled)